

IN THE CLAIMS

Amend claims 6, 10 and 27 as follows:

a¹
6. (Amended) The semiconductor switching circuit device of claim 5, wherein the substrate is made of a compound semiconductor and the resistor comprises a high dopant concentration region.

R²
10. (Amended) The semiconductor switching circuit device of claim 8, wherein a portion of the first transistor and a portion of the second transistor are disposed between the first and second input terminal pads, and wherein a portion of the third transistor and a portion of the fourth transistor are disposed between the third and fourth input terminal pads.

R³
27. (Amended) A semiconductor switching circuit device comprising:
four input terminal pads;
two common output terminal pads;
no more than two control terminal pads; and
two single pole double throw switches, each of the switches receiving two high frequency signals through two of the four input terminals and outputting one of the two high frequency signals to one of the two common output terminals in response to a control signal received from one of the control terminals.